L Number	Hits	Search Text	DB	Time stamp
1	1	@ad<=20010323 and epitaxial near grow near polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:20
34	693	@ad<=20010323 and 'epitaxial silicon' same 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:32
35	367	@ad<=20010323 and 'epitaxial silicon' with 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:41
36	9	@ad<=20010323 and 'epitaxial silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:41
37	1	@ad<=20010323 and 'multilayer silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:56
-	10	(("5393681") or ("6391692") or ("5308782") or ("5998248") or ("6319782")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 08:12
-	162	257/929 and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:59
-	542	438/300 and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 08:38
-	4	@ad<=20010323 and 'raised vertical lateral transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 16:02
-	1	@ad<=20010323 and 'raised source and drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:26
-	1	@ad<=20010323 and 'epitaxial' and 'source or drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:30
-	8	@ad<=20010323 and 'epitaxial' and 'source and drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:30
-	3470	gardner.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:45
-	6	gardner.inv. and 'vertical transistor' and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:48

–	4	@ad<=20010323 and 'elevated source and drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 16:06
–	257	@ad<=20010323 and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 16:06
–	37	@ad<=20010323 and 'epitaxial' with 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 08:56
–	1	"4728623".PN.	USPAT	2002/09/04 16:31
–	1	"4738937".PN.	USPAT	2002/09/04 16:31
–	1	"4918029".PN.	USPAT	2002/09/04 16:31
–	1	"5004702".PN.	USPAT	2002/09/04 16:31
–	1	"5030583".PN.	USPAT	2002/09/04 16:31
–	1	"5032538".PN.	USPAT	2002/09/04 16:31
–	1	"5045494".PN.	USPAT	2002/09/04 16:31
–	1	"5272109".PN.	USPAT	2002/09/04 16:32
–	1	"5496750".PN.	USPAT	2002/09/04 16:38
–	1	"5378651".PN.	USPAT	2002/09/04 16:38
–	1	"5321306".PN.	USPAT	2002/09/04 16:38
–	1	"5296388".PN.	USPAT	2002/09/04 16:38
–	1	"5250454".PN.	USPAT	2002/09/04 16:39
–	1	"5213991".PN.	USPAT	2002/09/04 16:39
–	1	"5079180".PN.	USPAT	2002/09/04 16:39
–	1	"5057899".PN.	USPAT	2002/09/04 16:39
–	1	"4966861".PN.	USPAT	2002/09/04 16:41
–	1	"4814841".PN.	USPAT	2002/09/04 16:48
–	1	"5057893".PN.	USPAT	2002/09/04 16:48
–	18	(("6096596") or ("6090691") or ("6057200") or ("6001697") or ("5998844") or ("5963822") or ("5945698") or ("5933738") or ("5863826")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 08:23
–	18	(("5831334") or ("5677573") or ("5641694") or ("5600161") or ("5497017") or ("5312768") or ("5156987") or ("5122476") or ("5087586")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 10:18
–	2	("5308782").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 10:19
–	2	("6319782").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 10:19
–	1731	((438/300) or (257/302) or (257/929) or (257/592)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 08:44
–	12	ri-seiko.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 08:44
–	38	@ad<=20010323 and 'epitaxial' with 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:33

-		263	@ad<=20010323 and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:33
-		263	@ad<=20010323 and elevated adj1 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:02
-		95	@ad<=20010323 and elevated adj1 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:02
-		112	@ad<=20010323 and raised adj1 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:03
-		229	@ad<=20010323 and raised adj1 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:03
-		0	@ad<=20010323 and 'epitaxial silicon gate' with 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:38
-		20	@ad<=20010323 and 'silicon gate' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:38
-		47	@ad<=20010323 and 'polysilicon gate' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:55
-		0	@ad<=20010323 and 'epitaxial polysilicon gate' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:06
-		1	@ad<=20010323 and 'epitaxial polysilicon' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 10:08
-		56	@ad<=20010323 and 'epitaxial polysilicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:20
-		0	@ad<=20010323 and 'epitaxial polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 14:05
-		24	@ad<=20010323 and 'epitaxial gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 14:05
-		24	@ad<=20010323 and 'epitaxial gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:30

–	560	@ad<=20010323 and polysilicon with epitaxial with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:16
–	2348	@ad<=20010323 and 'multilayer' same 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:55
–	260	(@ad<=20010323 and 'multilayer' same 'gate') and 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:18
–	0	@ad<=20010323 and 'multilayer gate' with 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:23